



General Description:

- (1) Chip Dimension
 Chip Size= 6 mil x 8 mil (170um x 220um)
 Chip Thickness = 100±10 μm
 P/N Bonding Pad = 70±5 μm
- (2) Electrode:
 P (Anode) → Au
 N (Cathode) → Au
- (3) Structure:
 Refer to drawing
 SiO₂ Passivated surface

Electro-optical Characteristics(Ta=RT)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Luminous Intensity	I _v	-	20	-	mcd	I _F = 5mA
		-	60	-	mcd	I _F =20mA
Forward Voltage	V _F	-	2.95	-	V	I _F = 5mA
		-	3.4	-	V	I _F =20mA
Dominant Wavelength	λ _D	-	460	-	nm	I _F = 5mA
		-	460	-	nm	I _F =20mA
Reverse Current	IR	0	-	2	μA	V _R =-5V

Features:

- 1. High Luminous Intensity
- 2. Long Operation Life
- 3. High Current; Pulse Operation
- 4. Indoor/Outdoor Applications

Notes:

- 1. Dominant wavelength includes an error of ± 1nm
- 2. Luminous intensity includes an error of ±10%
- 3. Luminous intensity is measured on bare chip
- 4. InGaN LED is sensitive to ESD